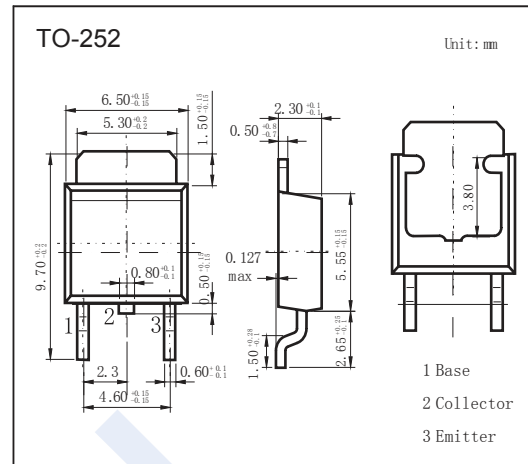


PNP Transistors

2SB967

■ Features

- Large collector current I_c
- Low collector to emitter saturation voltage $V_{CE(sat)}$.



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	-27	V
Collector - Emitter Voltage	V_{CEO}	-18	
Emitter - Base Voltage	V_{EBO}	-7	
Collector Current - Continuous	I_c	-5	A
Collector current -Pulse	I_{CP}	-8	
Collector Power Dissipation	P_c	20	W
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_c = -100 \mu\text{A}, I_E = 0$	-27			V
Collector- emitter breakdown voltage	V_{CEO}	$I_c = -1 \text{ mA}, I_B = 0$	-18			
Emitter - base breakdown voltage	V_{EBO}	$I_E = -100 \mu\text{A}, I_c = 0$	-7			
Collector-base cut-off current	I_{CBO}	$V_{CB} = -20\text{V}, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -5\text{V}, I_c = 0$			-1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_c = -3 \text{ A}, I_B = -100\text{mA}$			-1	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_c = -3 \text{ A}, I_B = -100\text{mA}$			-1.2	
DC current gain	h_{FE}	$V_{CE} = -2\text{V}, I_c = -2 \text{ A}$	90		625	
Collector output capacitance	C_{ob}	$V_{CB} = -20\text{V}, I_E = 0, f = 1\text{MHz}$			85	μF
Transition frequency	f_T	$V_{CE} = -6\text{V}, I_E = 50\text{mA}, f = 200\text{MHz}$		120		MHz

■ Classification of h_{FE}

Type	2SB967-P	2SB967-Q	2SB967-R
Range	90-135	125-205	180-625

PNP Transistors

2SB967

■ Typical Characteristics

